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FQB12P20 / FQI12P20

200V P-Channel MOSFET

General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

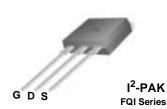
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters.

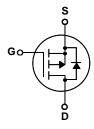
Features

- -11.5A, -200V, $R_{DS(on)} = 0.47\Omega @V_{GS} = -10 V$
- Low gate charge (typical 31 nC)
- Low Crss (typical 30 pF)
- Fast switching
- 100% avalanche tested
- · Improved dv/dt capability
- · RoHS Compliant









Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		FQB12P20 / FQI12P20	Units
V _{DSS}	Drain-Source Voltage		-200	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		-11.5	А
			-7.27	А
I _{DM}	Drain Current - Pulsed	(Note 1)	-46	А
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	810	mJ
I _{AR}	Avalanche Current	(Note 1)	-11.5	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.13	W
	Power Dissipation (T _C = 25°C)		120	W
	- Derate above 25°C		0.96	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.04	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *		40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

^{*} When mounted on the minimum pad size recommended (PCB Mount)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_{D} = -250 \mu\text{A}$	-200			V
ΔBV_{DSS}		VGS = 0 V, 1D = 200 μ/V	-200			V
/ ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -200 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
		V _{DS} = -160 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -5.75 A		0.36	0.47	Ω
g _{FS}	Forward Transconductance	V _{DS} = -40 V, I _D = -5.75 A (Note 4)		6.4		S
C _{iss}	Input Capacitance Output Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		920 190	1200 250	-
		f = 1.0 MHz				pF
C _{rss}	Reverse Transfer Capacitance			30	40	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -100 V, I _D = -11.5 A,		20	50	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		195	400	ns
t _{d(off)}	Turn-Off Delay Time	- NG - 20 22		40	90	ns
t _f	Turn-Off Fall Time	(Note 4, 5)		60	130	ns
Qg	Total Gate Charge	V _{DS} = -160 V, I _D = -11.5 A,		31	40	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		8.1		nC
Q _{gd}	Gate-Drain Charge	(Note 4, 5)		16		nC
Drain-S	Source Diode Characteristics a				-11.5	A
	Maximum Continuous Drain-Source Diode Forward Current Maximum Pulsed Drain-Source Diode Forward Current				-46	A
I _{SM}					_	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V, } I_{S} = -11.5 \text{ A}$			-5.0	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = -11.5 \text{ A},$ $dI_{C}/dt = 100 \text{ A/us}$ (Note 4)		180		ns
Q_{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$ (Note 4)		1.44		μC

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 9.2mH, I $_{AS}$ = -11.5A, V $_{DD}$ = -50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C 3. I $_{SD}$ ≤ -11.5A, di/dt ≤ 300A/ μ s, V $_{DD}$ ≤ BV $_{DSS}$, Starting T $_{J}$ = 25°C 4. Pulse Test : Pulse width ≤ 300 μ s, Duty cycle ≤ 2% 5. Essentially independent of operating temperature

Typical Characteristics

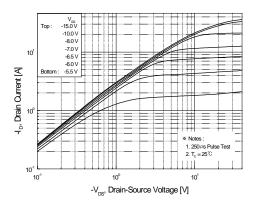


Figure 1. On-Region Characteristics

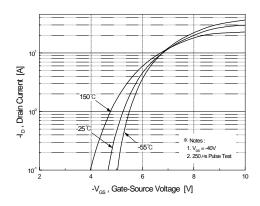


Figure 2. Transfer Characteristics

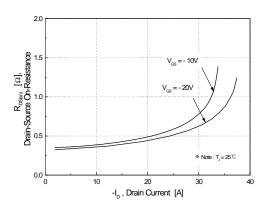


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

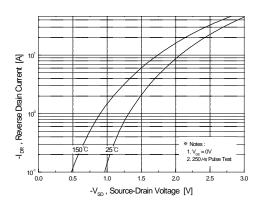


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

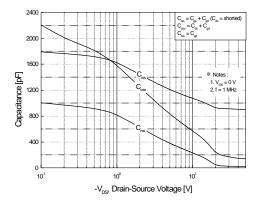


Figure 5. Capacitance Characteristics

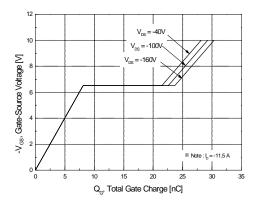
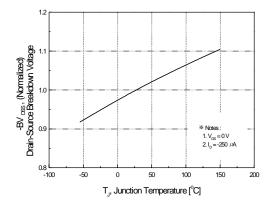


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)



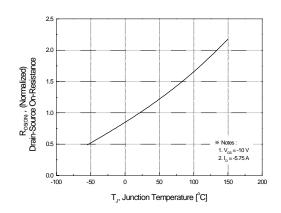
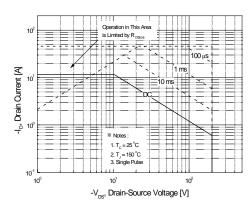


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



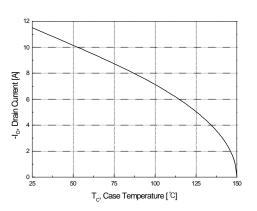


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

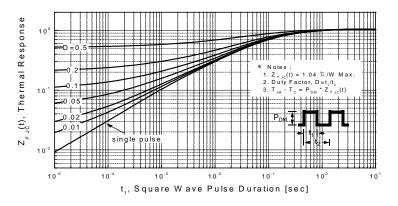
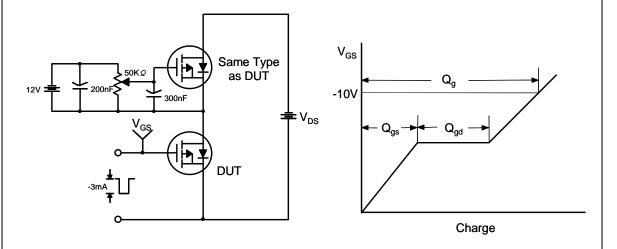


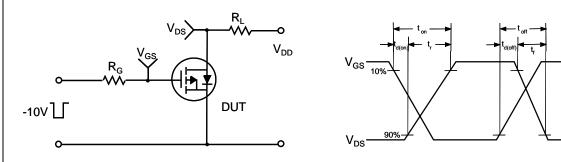
Figure 11. Transient Thermal Response Curve

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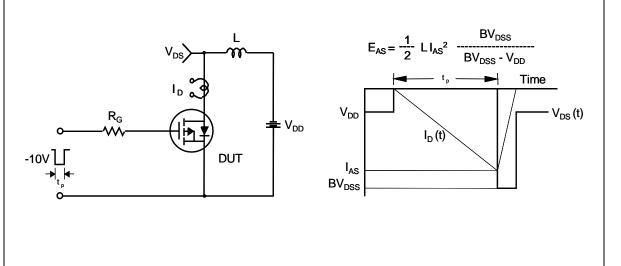
Gate Charge Test Circuit & Waveform



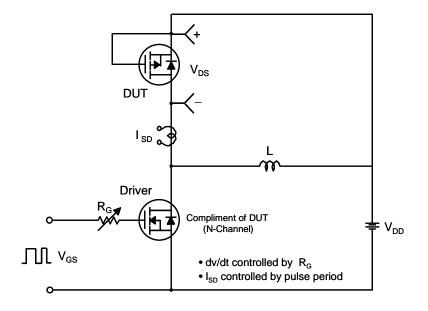
Resistive Switching Test Circuit & Waveforms

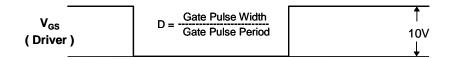


Unclamped Inductive Switching Test Circuit & Waveforms

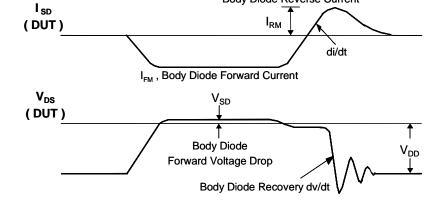


Peak Diode Recovery dv/dt Test Circuit & Waveforms





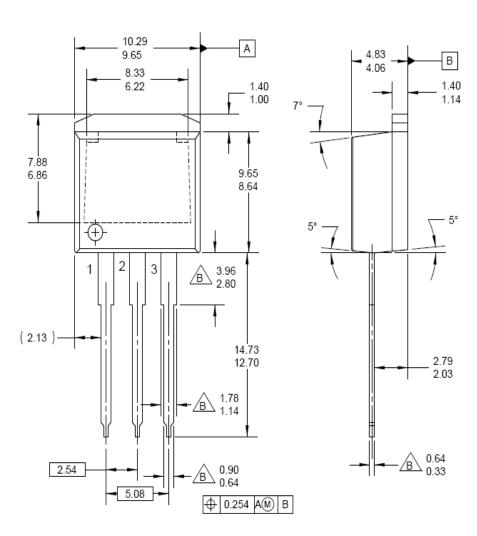
Body Diode Reverse Current



Mechanical Dimensions D² - PAK -A-9.65 8.38 9.00 MIN 1.78 MAX 10.00 (2.12) -1.50 MIN 5.08 ♦ 0.25 M B AM LAND PATTERN RECOMMENDATION -B--6.22 MIN-1.65 -1.14 6.86 MIN 15.88 14.61 SEE DETAIL A GAGE PLANE 0.25 0.10 B .25 MAX SEATING PLANE DETAIL Dimensions in Millimeters

Mechanical Dimensions

I² - PAK



Dimensions in Millimeters





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